

Amendments to the Specification

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Abstract

~~Patterning method, and field effect transistors~~

~~An explanation is given of, inter alia, a~~ patterning method, ~~in which~~ with a filling material ~~(22)~~ with a T-shaped cross section is used as a mask during patterning in order to produce structures having sublithographic dimensions, ~~in particular~~ such as a double-fin field effect transistor.

~~(Figure 1B)~~